

## **isc** Silicon PNP Darlington Power Transistor

# **MJE702**

### DESCRIPTION

- DC Current Gain—
  - : h<sub>FE</sub> = 2000(TYP) @ I<sub>C</sub>= -2A
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### **APPLICATIONS**

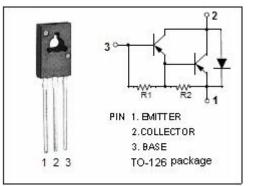
Designed for general-purpose amplifier and low-speed switching applications

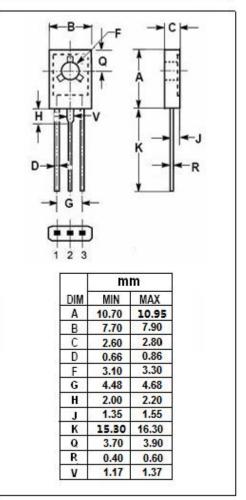
$ABSOLUTE MAXIMUM RATINGS(T_a=25C)$						
SYMBOL	PARAMETER VALUE		UNIT			
V <sub>сво</sub>	Collector-Base Voltage	-80	V			
V <sub>CEO</sub>	Collector-Emitter Voltage	-80	V			
$V_{\text{EBO}}$	Emitter-Base Voltage	-5	V			
lc	Collector Current-Continuous	-4	А			
I <sub>B</sub>	Base Current	-0.1	А			
Pc	Collector Power Dissipation $T_c=25^{\circ}C$	40	W			
Ti	Junction Temperature	150	°C			
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C			

### ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case		°C/W





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### **ELECTRICAL CHARACTERISTICS**

#### $T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	МАХ	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -50mA; I <sub>B</sub> = 0	-80		V
V <sub>CE(sat)-1</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -1.5A; I <sub>B</sub> = -30mA		-2.5	V
V <sub>CE(sat)-2</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -4A; I <sub>B</sub> = -40mA		-3.0	V
V <sub>BE(on)-1</sub>	Base-Emitter On Voltage	I <sub>C</sub> = -1.5A; V <sub>CE</sub> = -3V		-2.5	V
V <sub>BE(on)-2</sub>	Base-Emitter On Voltage	I <sub>C</sub> = -4A; V <sub>CE</sub> = -3V		-3.0	V
Iceo	Collector Cutoff Current	V <sub>CE</sub> = -80V; I <sub>B</sub> = 0		-0.1	mA
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = -80V; I <sub>E</sub> = 0 V <sub>CB</sub> = -80V; I <sub>E</sub> = 0;T <sub>C</sub> = 100°C		-0.1 -0.5	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -5V; I <sub>C</sub> = 0		-2.0	mA
h <sub>FE-1</sub>	DC Current Gain	Ic= -1.5 A ; Vce= -3V	750		
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = -4A ; V <sub>CE</sub> = -3V	100		

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